## Layout Decomposition for Spacer-is-Metal (SIM) Self-Aligned Double Patterning

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## **LELE Double Patterning Lithography**

 Litho-etch-litho-etch (LELE) double patterning lithography (DPL) has been widely known and used in industry



# Self-Aligned Double Patterning (SADP)

- Self-aligned double patterning (SADP) becomes more popular due to the better overlay and critical dimension (CD) controllability
- Processes in SADP
  - Positive: spacers define lines
  - Negative: spacers define trenches



## Layout Decomposition in SADP

- Layout decomposition (LD) in SADP
  - Spacer-is-metal (SIM): spacers define patterns
  - Spacer-is-dielectric (SID): spacers define spacings among patterns





## SIM-Type vs. SID-Type 2D LD

#### SID-type 2D layout decomposition

- Patterns are formed by either core patterns or assist core patterns
- Patterns with arbitrary spacing values may be distorted after LD



# SIM-Type vs. SID-Type 2D LD

#### □ SID-type 2D layout decomposition

- Patterns are formed by either core patterns or assist core patterns
- Patterns with arbitrary spacing values may be distorted after LD
- SIM-type 2D layout decomposition
  - Patterns are formed by spacers
  - May have better decomposability since non-uniform spacings can be controlled by core patterns



## **Cut Pattern Determination**

- Cut patterns are used to remove spacers not covering layout patterns
- A cut pattern can be immediately determined as a core pattern is chosen



## **Previous Studies**

SID-type layout decomposition

- Ban et al., "Flexible 2D layout decomposition framework for spacer-type double patterning lithography," in *DAC-2011*
- Zhang et al., "Self-aligned double patterning decomposition for overlay minimization and hot spot detection," in *DAC-2011*
- Xiao et al., "A polynomial time exact algorithm for self-aligned double patterning layout decomposition," in *ISPD-2012*

#### SIM-type layout decomposition

- Zhang et al., "Effective decomposition algorithm for self-aligned double patterning lithography," in SPIE-2011
  - A SAT-based algorithm (NP-complete)
  - Not applicable to indecomposable designs

## **SIM-Type Layout Decomposition**

#### Terminologies

- A core conflict: a pair of core patterns with distance <  $dis_{core}$
- A cut conflict: a pair of cut patterns with distance  $< dis_{cut}$

#### Problem formulation

- Given: a photomask layout
- **Objective**: a layout decomposition result with minimized #conflicts
  - A layout decomposition result = a core mask + a cut mask
  - #conflicts = #core conflicts + #cut conflicts
- Constraint: the produced layout is exactly the same as the original one





## **Core Candidate Identification**

- Core candidates are identified for spacer deposition
  - Fragment polygons into rectangles (features)
  - Identify two core candidates for each feature



## **Core-Feature Matching Graph Construction**

- $\Box$  Construct a core-feature matching graph  $G_M$ 
  - A feature vertex u: a feature
  - A core vertex v: a core candidate
  - An edge (u, v): v is a core candidate of u
- Merge equivalent vertices to reduce graph complexity



## **Conflict Graph Construction**

- Inspect conflicts among core candidates
  - The distance between two core candidates  $< dis_{core}$
  - The two core candidates cannot be merged
- $\Box$  Construct a conflict graph  $G_C$ 
  - A vertex v: a core candidate
  - An edge  $(v_i, v_j)$ :  $v_i$  and  $v_j$  are conflicting



## **Conflict Graph Construction (cont'd)**

- Inspect conflicts among cut patterns
  - The distance between two cut patterns  $< dis_{cut}$
  - The two cut patterns cannot be merged
- $\Box$  Update the conflict graph  $G_C$ 
  - A vertex v: a core candidate
  - An edge  $(v_i, v_j)$ :  $v_i$  and  $v_j$  are conflict or two corresponding cut patterns are conflict



## **Graph Formulation**

□ Construct the combination graph G of a core-feature matching graph  $G_M$  and a conflict graph  $G_C$ 

#### Problem Constrained Set Covering Problem (SCP)

- Given: a combination graph
- **Objective:** a set cover  $\mathbb{C}$  with the minimized #conflicts
  - A set cover  $\mathbb{C}$  : a set of core vertices
  - #conflicts: #conflict edges within  ${\ensuremath{\mathbb C}}$
- Constraint: all feature vertices are covered by  $\mathbb C$





## **Initial Solution Derivation**

- Greedy principle: select the most cost-effective core vertex into the set cover C at a time
  - covering( $v_i$ ): #uncovered feature vertices covered by  $v_i$
  - $conflict(v_i)$  : increased #conflict edges due to the addition of  $v_i$  into  $\mathbb C$
  - $effectiveness(v_i) = covering(v_i) \alpha \cdot conflict(v_i)$

#### □ <u>Algorithm</u> Greedy Algorithm for Constrained SCP

<u>Step 1</u> Compute *effectiveness*( $v_i$ ) for each core vertex  $v_i$ <u>Step 2</u> Add  $v_j$  with the largest *effectiveness*( $v_j$ ) into  $\mathbb{C}$ <u>Step 3</u> Update *covering*( $v_i$ ) and *conflict*( $v_i$ ) for each  $v_i \in \overline{\mathbb{C}}$ Repeat Steps 1 to 3 until all feature vertices are covered

## **Example of the Greedy Algorithm**

 $\square effectiveness(v_i) = covering(v_i) - 0.5 \cdot conflict(v_i)$ 





## **F-M Heuristic**

- The solution refinement algorithm is based on the F-M partitioning heuristic [Fiduccia and Mattheyses, DAC'82]
  - Objective: minimize #cut edges in a partition
  - In each step, move a vertex with the largest gain and lock it
    - $gain(v) = -\Delta edge\_cut(v)$
  - In each iteration, choose the partition with the maximum partial sum of gains as the refinement solution



## **Partition-Based Solution Refinement**

- Solution refinement for the constrained SCP
  - **Initial partition:** the initial solution from the greedy algorithm
  - **Objective:** minimize # conflicts in the set cover  $\mathbb{C}$  of a partition
  - Constraint: the refinement solution (a partition with the maximum partial sum) must be legal in each iteration
    - A legal partition: all feature vertices are covered by the corresponding set cover C



#### Partition-Based Solution Refinement (cont'd)

- Solution legalization by gain setting
  - Vertex gain:  $gain(v) = -\Delta conflict(v) \beta \times \Delta uncover(v)$ 
    - $\Delta conflict(v)$ : variation of #conflicts due to the movement of v
    - $\Delta uncover(v)$ : variation of #uncovered feature vertices
  - **Theorem** By setting  $\beta > 2d$ , the partition-based algorithm can always find a legal refinement solution in each iteration
    - *d*: maximum #conflict edges incident to a core vertex



An illegal partition

## **Example of Solution Refinement**





## **Experimental Setup**

- Platform
  - C++ programming language
  - 2.13 GHz Linux workstation with 48 GB memory
- Benchmark
  - ISCAS-89 circuits
  - Routing wires in Metal-2, 2D gridless layouts, uniform wire width
  - Indecomposable layouts (previous study [Zhang et al., SPIE'11] is not applicable)
- Comparison
  - A random algorithm for the constrained SCP was implemented
  - Core vertices covering some uncovered feature vertices are randomly and sequentially selected

## **Experimental Results and Conclusion**

- The greedy heuristic generates 7X fewer conflicts than the random method
- □ The partition-based solution refinement further reduce 84.7% #conflicts
- Our algorithms can effectively derive an SIM-type layout decomposition solution with desired numbers of core conflicts.



## **Layout Decomposition Result**

□ A local view of the layout decomposition result of s5378





## Conclusions

- This paper proposes an efficient graph-based SIM-type layout decomposition algorithm for SADP
- The decomposition problem is transformed into a constrained SCP and solved with efficient heuristic algorithms
- Experimental results have shown that our algorithms can effectively derive good SIM-type layout decomposition solutions